DE 9097250 0007844 7

9097250 TOSHIBA (DISCRETE/OPTO)

SILICON NPN TRIPLE DIFFUSED TYPE

566 07844 UT-33-09

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

FEATURES :

- . High DC Current Gain
 - : $h_{FE}=300 (Max.) (V_{CE}=5V, I_{C}=0.5A)$
- . Low Saturation Voltage
 - : V_{CE}(sat)=1.0V(Max.)(IC=3A, IB=0.3A)
- . High Power Dissipation : P_C=30W (Tc=25°C)
- . Complementary to 2SB834.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltag	ge	v _{CBO}	60	V	
Collector-Emitter Vol	tage	VCEO	60	V	
Emitter-Base Voltage		v_{EBO}	7	· v	
Collector Current		IC	3	A	
Base Current		IB	0.5	A,	
Collector Power Dissipation	Ta=25°C	Tj	1.5	w ·	
	Tc=25°C	-1	30		
Junction Temperature	WILL	Тj	150	°C	
Storage Temperature Range		T _{stg}	-55∿150	· °C	

	Unit in
10.3MA)	153MAX.
2076	130MIN.
254	2.54 XX
1. BASE 2. COLLE 3. EMITT	CCTOR (HEAT SINK)
JEDEC	TO-220AB
EIAJ	SC-46
TOSHIBA	2-10A1A

Mounting kit No. AC75 Weight: 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} =60V, I _E =0	W	-	100	μA
Emitter Cut-off Current		I_{EBO}	V _{EB} =7V, I _C =0	-	_	100	μA
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	I _C =50mA, I _B =0	60	N-	-	v
DC Current Gain		hFE	$V_{CE}=5V$, $I_{C}=0.5A$ (Note)	60		300	- XI
Collector Emitter Saturation Voltage		VCE(sat)	I _C =3A, I _B =0.3A	OM	0.25	1.0	v
Base-Emitter Voltage		VBE	V _{CE} =5V, I _C =0.5A	~ON	0.7	1.0	v
Transition Frequency		$\mathbf{f_{T}}$	V _{CE} =5V, I _C =0.5A	-51	3.0	-	MHz
Collector Output Capacitance		Ссь	V _{CB} =10V, I _E =0, f=1MHz	CY	70	W _	pF
Switching Time	Turn-on Time	ton	$I_{B1} = I_{B2} = 0.2 \text{ A}$ DUTY CYCLE < 1%	I.C	0.8	TVI	
	Storage Time	t _{stg}		215	1.5	TW	μs
	Fall Time	tf		007	0.8	_	

Note: hFE Classification $60 \sim 120$, Y: $100 \sim 200$, GR: $150 \sim 300$.

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